(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
13 October 2005 (13.10.2005)

PCT

(10) International Publication Number
WO 2005/096383 A1

(51) International Patent Classification[7]: H01L 27/146

(21) International Application Number:
PCT/CH2005/000184

(22) International Filing Date: 31 March 2005 (31.03.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
04007760.4 31 March 2004 (31.03.2004) EP

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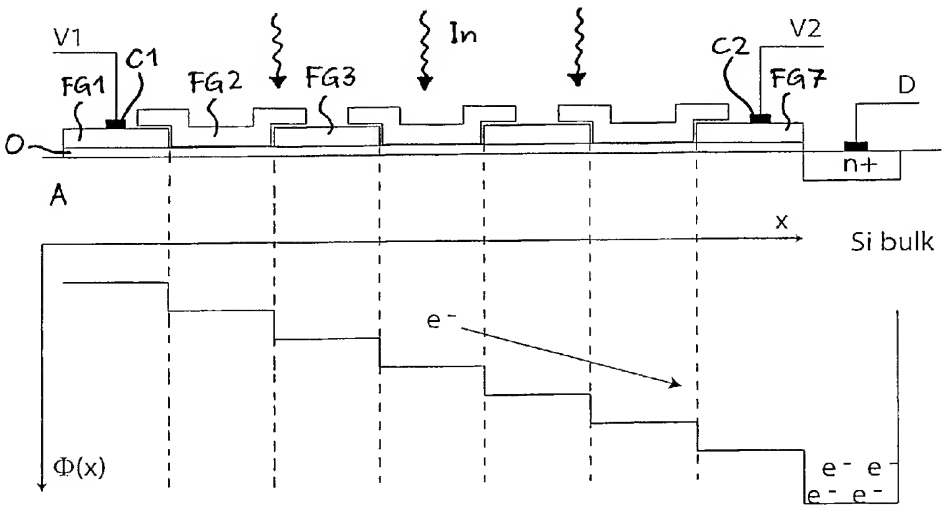
(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

[Continued on next page]

(54) **Title:** IMAGE SENSOR WITH LARGE-AREA, HIGH-SENSITIVITY AND HIGH-SPEED PIXELS



(57) **Abstract:** The pixel for use in an image sensor comprises a low-doped semiconductor substrate (A). On the substrate (A), an arrangement of a plurality of floating areas, e.g., floating gates (FG2-FG6), is provided. Neighboring floating gates are electrically isolated from each other yet capacitively coupled to each other. By applying a voltage (V2 - V1) to two contact areas (FG1, FG7), a lateral steplike electric field is generated. Photogenerated charge carriers move along the electric-field lines to the point of highest potential energy, where a floating diffusion (D) accumulate the photocharges. The charges accumulated in the various pixels are sequentially read out with a suitable circuit known from image-sensor literature, such as a source follower or a charge amplifier with row and column select mechanisms. The pixel of offers at the same time a large sensing area, a high photocharge-detection sensitivity and a high response speed, without any static current consumption.

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